

NEW CLAIMS

1. (Amended) A copper or copper alloy target/copper alloy backing plate assembly for use in magnetron sputtering, wherein the copper alloy backing plate is formed from low beryllium copper alloy containing 0.2 to 0.5wt% of Be, or Cu-Ni-Si alloy containing 2 to 4wt% of Ni and 0.3 to 0.9wt% of Si or Cu-Ni-Si-based alloy containing 2 to 4wt% of Ni and 0.3 to 0.9wt% of Si.
2. The copper or copper alloy target/copper alloy backing plate assembly according to claim 1, wherein the Cu-Ni-Si-based alloy backing plate is formed from Cu-Ni-Si-based alloy containing 2 to 4wt% of Ni, 0.3 to 0.9wt% of Si, 0.1 to 0.9wt% of Cr or 0.1 to 0.9wt% of Mg.
3. (Deleted)
4. The copper or copper alloy target/copper alloy backing plate assembly according to claim 1 or claim 2, wherein the copper alloy backing plate has an electrical conductivity of 35 to 60% (IACS), and 0.2% proof stress of 400 to 850MPa.
5. The copper or copper alloy target/copper alloy backing plate assembly according to any one of claims 1 to 4, wherein the copper or copper alloy target/copper alloy backing plate assembly is diffusion bonded.
6. The copper or copper alloy target/copper alloy backing plate assembly according to claim 5, wherein the diffusion bonding temperature is 175 to 450°C.

The Statement under Article 19(1) PCT

In the claim 1, the description "Cu-Ni-Si-based alloy" in which the amount of component was not specified was amended to "Cu-Ni-Si-based alloy containing 2 to 4wt% of Ni and 0.3 to 0.9wt% of Si". Thus, alloy content was amended to be consistent with the description in the Description.

The claim 3 specifically did not restrict the component composition of copper alloy. When the component composition of copper alloy is restricted so as to conform with the description in the Description, the claim 3 and the claim 4 overlaps. Accordingly, the claim 3 was deleted.

Mis-description in the claims can be overcome with the above corrections.